NUF4000MU

4-Channel EMI Filter with Integrated ESD Protection

The NUF4000MU is a four−channel (C−R−C) Pi−style EMI filter array with integrated ESD protection. Its typical component values of R = 100 Ω and C = 15 pF deliver a cutoff frequency of 105 MHz and stop band attenuation greater than −30 dB from 800 MHz to 5.0 GHz.

This performance makes the part ideal for parallel interfaces with data rates up to 70 Mbps in applications where wireless interference must be minimized. The specified attenuation range is very effective in minimizing interference from 2G/3G, GPS, Bluetooth® and WLAN signals.

The NUF4000MU is available in the low−profile 8−lead 1.2x1.8mm UDFN8 surface mount package.

Features/Benefits

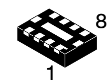
- ±8.0 kV ESD Protection on each channel (IEC61000−4−2 Level 4, Contact Discharge)
- R/C Values of 100 Ω and 15 pF deliver Exceptional S21 Performance Characteristics of 105 MHz f_{3dB} and −30 dB Stop Band Attenuation from 800 MHz to 5.0 GHz
- Integrated EMI/ESD System Solution in UDFN Package Offers Exceptional Cost, System Reliability and Space Savings
- This is a Pb−Free Device

Applications

- EMI Filtering for LCD and Camera Data Lines
- EMI Filtering and Protection for I/O Ports and Keypads

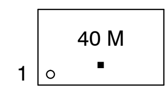
ON Semiconductor®

http://onsemi.com



UDFN8
CASE 517AD

MARKING DIAGRAM

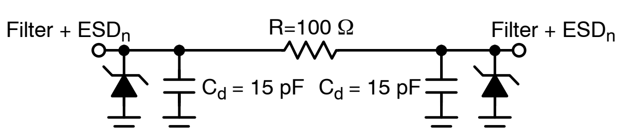


40	= Specific Device Code
M	= Assembly and Date Code
▪	= Pb−Free Package

ORDERING INFORMATION

Device	Package	Shipping†
NUF4000MUT2G	UDFN8 (Pb−Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



See Table 1 for pin description

Figure 1. Electrical Schematic

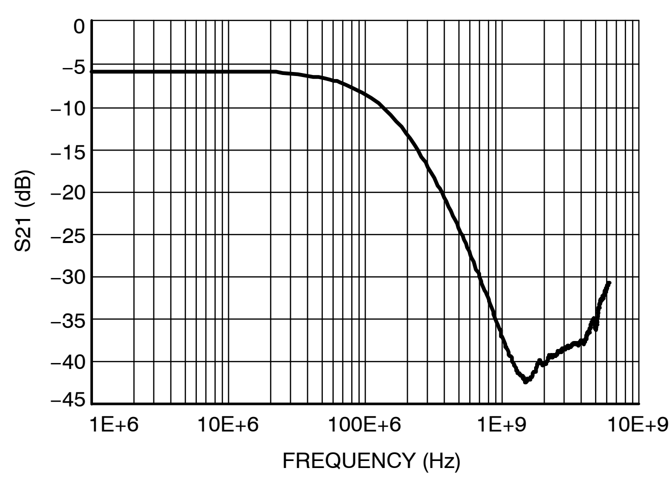
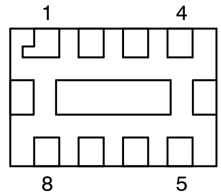


Figure 2. Typical Insertion Loss Curve



(Bottom View)

Figure 3. Pin Diagram

Table 1. FUNCTIONAL PIN DESCRIPTION

Filter	Device Pins	Description
Filter 1	1 & 8	Filter + ESD Channel 1
Filter 2	2 & 7	Filter + ESD Channel 2
Filter 3	3 & 6	Filter + ESD Channel 3
Filter 4	4 & 5	Filter + ESD Channel 4
Ground Pad	GND	Ground

MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
ESD Discharge IEC61000−4−2 Contact Discharge	V_{PP}	8.0	kV
Operating Temperature Range	T_{OP}	−40 to 85	°C
Storage Temperature Range	T_{STG}	−55 to 150	°C
Maximum Lead Temperature for Soldering Purposes (1.8 in from case for 10 seconds)	T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Maximum Reverse Working Voltage	V_{RWM}				5.0	V
Breakdown Voltage	V_{BR}	I_R = 1.0 mA	6.0	7.0	8.0	V
Leakage Current	I_R	V_{RWM} = 3.3 V			100	nA
Resistance	R_A	I_R = 10 mA	85	100	115	Ω
Diode Capacitance	C_d	V_R = 2.5 V, f = 1.0 MHz		15	20	pF
Line Capacitance	C_L	V_R = 2.5 V, f = 1.0 MHz		30	40	pF
3 dB Cut−Off Frequency (Note 1)	f_{3dB}	Above this frequency, appreciable attenuation occurs		105		MHz
6 dB Cut−Off Frequency (Note 1)	f_{6dB}	Above this frequency, appreciable attenuation occurs		180		MHz

1. 50 Ω source and 50 Ω load termination.

TYPICAL PERFORMANCE CURVES (T_A= 25°C unless otherwise specified)

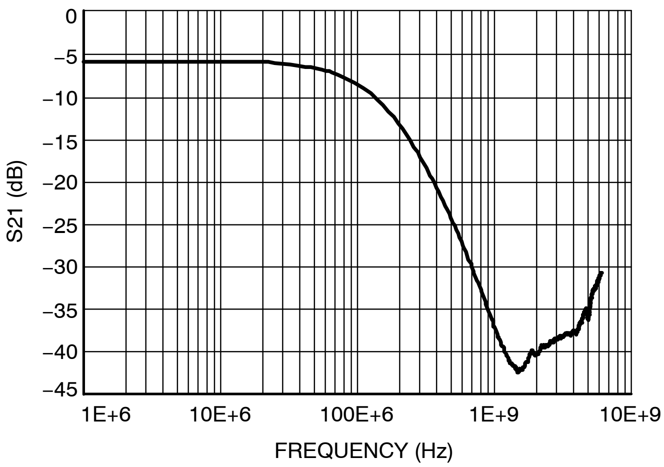


Figure 4. Insertion Loss Characteristic

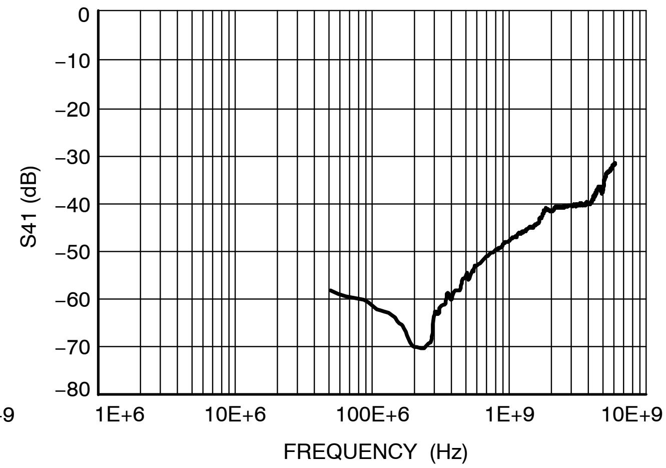


Figure 5. Insertion Loss Characteristic

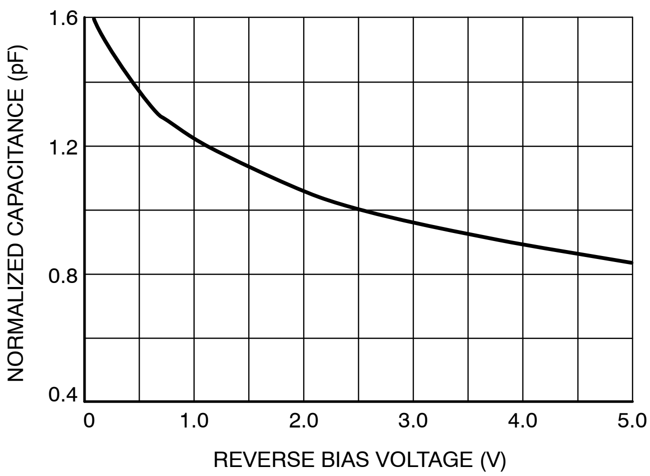


Figure 6. Typical Capacitance vs. Reverse Biased Voltage (Normalized Capacitance Cd at 2.5 V)

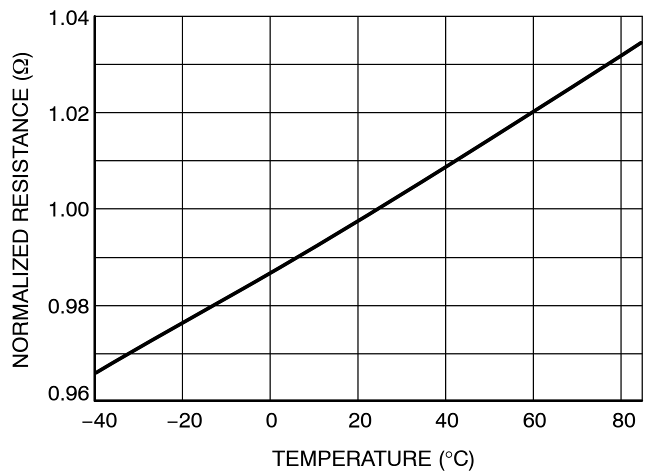


Figure 7. Typical Resistance over Temperature

Theory of Operation

The NUF4000MU combines ESD protection and EMI filtering conveniently into a small package for today's size constrained applications. The capacitance inherent to a typical protection diode is utilized to provide the capacitance value necessary to create the desired frequency response based upon the series resistance in the filter. By combining this functionality into one device, a large number of discrete components are integrated into one small package saving valuable board space and reducing BOM count and cost in the application.

Application Example

The accepted practice for specifying bandwidth in a filter is to use the 3 dB cutoff frequency. Utilizing points such as the 6 dB or 9 dB cutoff frequencies results in signal degradation in an application. This can be illustrated in an application example. A typical application would include EMI filtering of data lines in a camera or display interface. In such an example it is important to first understand the signal and its spectral content. By understanding these things, an appropriate filter can be selected for the desired application. A typical data signal is pattern of 1's and 0's transmitted over a line in a form similar to a square wave. The maximum frequency of such a signal would be the pattern 1-0-1-0 such that for a signal with a data rate of 100 Mbps, the maximum frequency component would be 50 MHz. The next item to consider is the spectral content of the signal, which can be understood with the Fourier series approximation of a square wave, shown below in Equations 1 and 2 in the Fourier series approximation.

From this it can be seen that a square wave consists of odd order harmonics and to fully construct a square wave n must go to infinity. However, to retain an acceptable portion of the waveform, the first two terms are generally sufficient. These two terms contain about 85% of the signal amplitude and allow a reasonable square wave to be reconstructed. Therefore, to reasonably pass a square wave of frequency *x* the minimum filter bandwidth necessary is *3x*. All ON Semiconductor EMI filters are rated according to this principle. Attempting to violate this principle will result in significant rounding of the waveform and cause problems in transmitting the correct data. For example, take the filter with the response shown in Figure 8 and apply three different data waveforms. To calculate these three different frequencies, the 3 dB, 6 dB, and 9 dB bandwidths will be used.

Equation 1:

$$x(t) = \frac{1}{2} + \frac{2}{\pi} \sum_{n=1}^{a} \left[\frac{1}{2n-1} \sin((2n-1)\omega_0 t) \right] \quad \text{(eq. 1)}$$

Equation 2 (simplified form of Equation 1):

$$x(t) = \frac{1}{2} + \frac{2}{\pi} \left[\frac{\sin(\omega_0 t)}{1} + \frac{\sin(3\omega_0 t)}{3} + \frac{\sin(5\omega_0 t)}{5} + \ldots \right] \text{(eq. 2)}$$

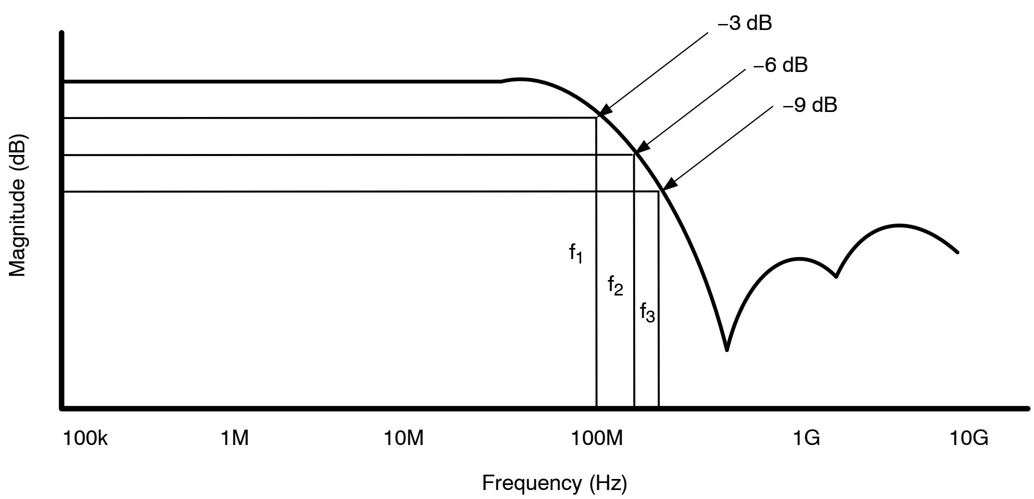


Figure 8. Filter Bandwidth

From the above paragraphs it is shown that the maximum supported frequency of a waveform that can be passed through the filter can be found by dividing the bandwidth by a factor of three (to obtain the corresponding data rate multiply the result by two). The following table gives the bandwidth values and the corresponding maximum supported frequencies and the third harmonic frequencies.

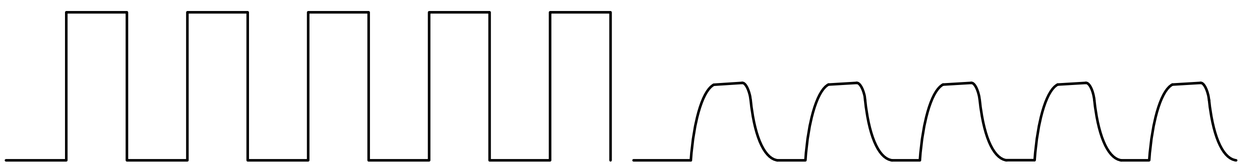
Table 2. Frequency Chart

Bandwidth	Maximum Supported Frequency	Third Harmonic Frequency
3 dB–100 MHz	33.33 MHz (f_1)	100 MHz
6 dB–200 MHz	66.67 MHz (f_2)	200 MHz
9 dB–300 MHz	100 MHz (f_3)	300 MHz

Considering that 85% of the amplitude of the square is in the first two terms of the Fourier series approximation most of the signal content is at the fundamental (maximum supported) frequency and the third harmonic frequency. If a signal with a frequency of 33.33 MHz is input to this filter, the first two terms are sufficiently passed such that the signal is only mildly affected, as is shown in Figure 9a. If a signal with a frequency of 66.67 MHz is input to this same filter, the third harmonic term is significantly attenuated. This serves to round the signal edges and skew the waveform, as is shown in Figure 9b. In the case that a 100 MHz signal is input to this filter, the third harmonic term is attenuated even further and results in even more rounding of the signal edges as is shown in Figure 9c. The result is the degradation of the data being transmitted making the digital data (1's and 0's) more difficult to discern. This does not include effects of other components such as interconnect and other path losses which could further serve to degrade the signal integrity. While some filter products may specify the 6 dB or 9 dB bandwidths, actually using these to calculate supported frequencies (and corresponding data rates) results in significant signal degradation. *To ensure the best signal integrity possible, it is best to use the 3 dB bandwidth to calculate the achievable data rate.*

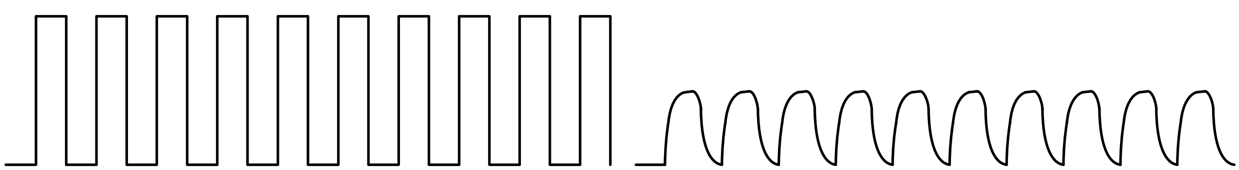
Input Waveform **Output Waveform**

a) Frequency = f_1



Input Waveform **Output Waveform**

b) Frequency = f_2



Input Waveform **Output Waveform**

c) Frequency = f_3

Figure 9. Input and Output Waveforms of Filter

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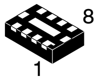
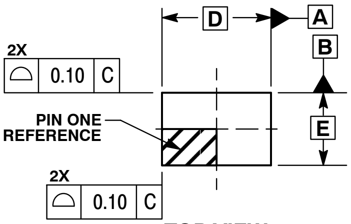
UDFN8 1.8x1.2, 0.4P
CASE 517AD
ISSUE D

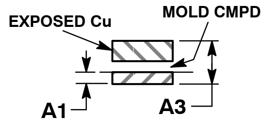
DATE 23 OCT 2012



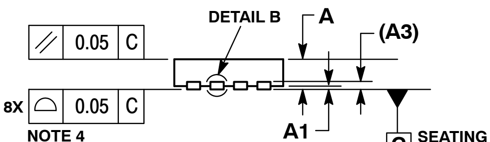
SCALE 4:1



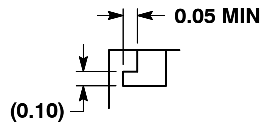
TOP VIEW



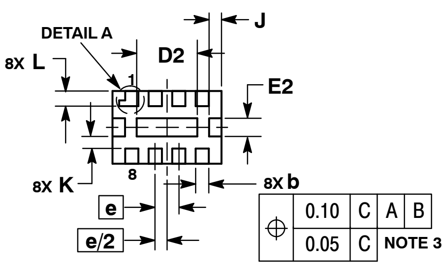
DETAIL B
ALTERNATE CONSTRUCTIONS



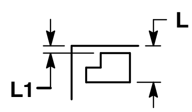
SIDE VIEW



DETAIL A



BOTTOM VIEW

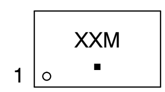


DETAIL A
OPTIONAL CONSTRUCTION

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30 mm FROM TERMINAL.
4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS.

	MILLIMETERS	
DIM	MIN	MAX
A	0.45	0.55
A1	0.00	0.05
A3	0.13 REF	
b	0.15	0.25
D	1.80 BSC	
E	1.20 BSC	
e	0.40 BSC	
D2	0.90	1.10
E2	0.20	0.30
J	0.19 REF	
K	0.20 TYP	
L	0.20	0.30
L1	---	0.10

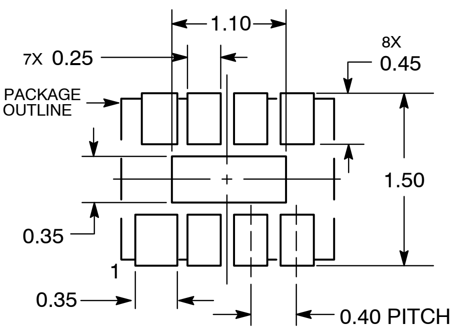
GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G”, may or not be present.

SOLDERING FOOTPRINT*



DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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DESCRIPTION:	UDFN8 1.8X1.2, 0.4P	PAGE 1 OF 1

ADDITIONAL INFORMATION

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